VS-HFA04SD60S-M3

Vishay Semiconductors

HEXFRED[®], Ultrafast Soft Recovery Diode, 4 A

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PRODUCT SUMMARY	
Package	TO-252AA (D-PAK)
I _{F(AV)}	4 A
V _R	600 V
V _F at I _F	1.4 V
t _{rr} typ.	17 ns
T _J max.	150 °C
Diode variation	Single die

FEATURES

- Ultrafast recovery time
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- · Guaranteed avalanche
- HALOGEN Specified at operating temperature FREE Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION / APPLICATIONS

These diodes are optimized to reduce losses and EMI / RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for freewheeling, flyback, power converters, motor drives, and other applications where high speed and reduced switching losses are design requirements.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V _{RRM}		600	V					
Maximum continuous forward current	I _{F(AV)}	T _C = 100 °C	4						
Single pulse forward current	I _{FSM}		25	А					
Repetitive peak forward current	I _{FRM}	T _C = 116 °C	16						
Maximum power dissipation	PD	T _C = 100 °C	10	W					
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +150	C°					

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS MIN. TYP. MAX.								
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-					
Forward voltage See fig. 1	V _F	$I_F = 4 A$	-	1.5	1.8	V				
		I _F = 8 A	-	1.8	2.2					
		I _F = 4 A, T _J = 125 °C	-	1.4	1.7					
Maximum reverse		$V_{\rm R} = V_{\rm R}$ rated	-	0.17	3.0					
leakage current		$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	-	44	300	μΑ				
Junction capacitance	CT	V _R = 200 V	-	4	8	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH				

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COMPLIANT



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DYNAMIC RECOVERY CHARACTERISTICS ($T_C = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 1.0 \text{ A}$	-	17	-				
Reverse recovery time	t _{rr}	T _J = 25 °C		-	28	42	ns		
		T _J = 125 °C	I _F = 4 A dI _F /dt = 200 A/μs V _B = 200 V	-	38	57			
Deal and a second	I _{RRM}	$T_J = 25 \ ^\circ C$		-	2.9	5.2	A		
Peak recovery current		T _J = 125 °C		-	3.7	6.7			
	Q _{rr}	T _J = 25 °C		-	40	60	nC		
Reverse recovery charge		T _J = 125 °C		-	70	105			
Rate of fall of recovery current	dl _{(rec)M} /dt	T _J = 25 °C		-	280	-	A /uo		
		T _J = 125 °C		-	235	-	A∕µs		

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	150	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	5.0	°C/W				
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	0/11				
Weight			-	2.0	-	g				
weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-252AA (D-PAK)	HFA04SD60S							



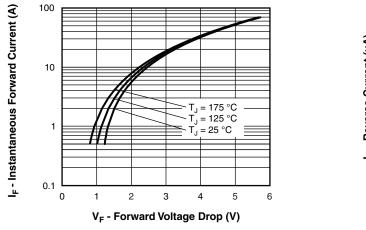


Fig. 1 - Typical Forward Voltage Drop Characteristics

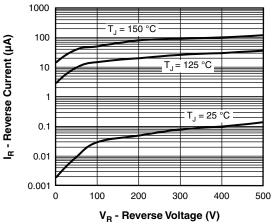


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

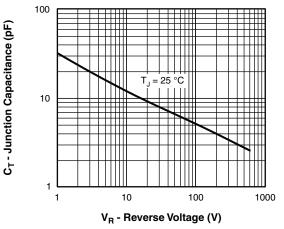


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

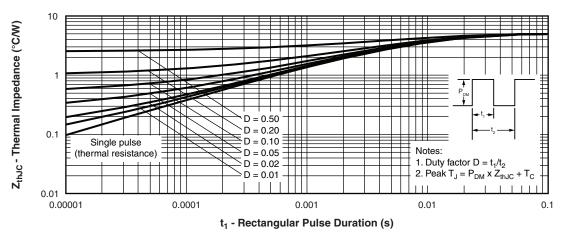


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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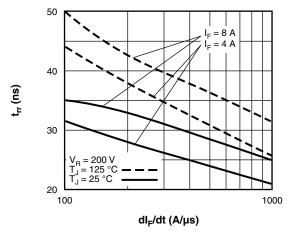
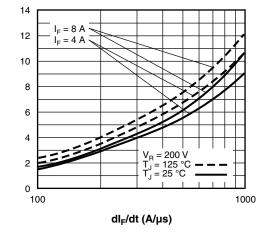


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt



I_{RR} (A)

Fig. 6 - Typical Recovery Current vs. dl_F/dt

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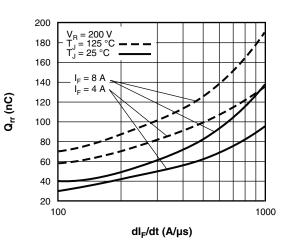


Fig. 7 - Typical Stored Charge vs. dl_F/dt

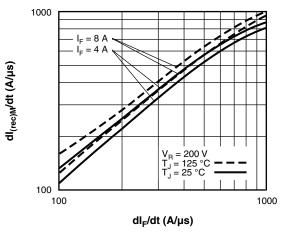


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt

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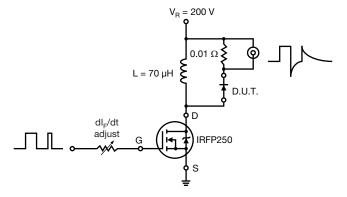
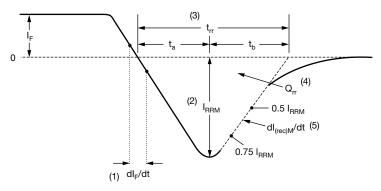


Fig. 9 - Reverse Recovery Parameter Test Circuit



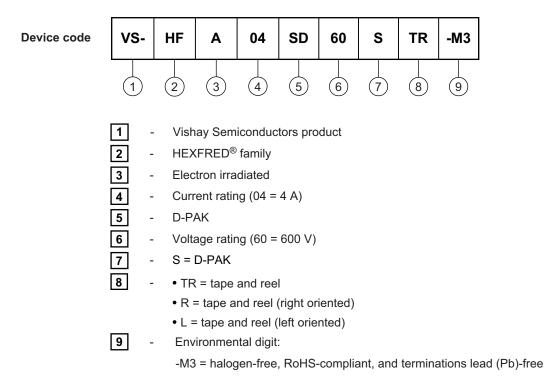
- (1) dI_F/dt rate of change of current through zero crossing
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (5) dl_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}

 $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

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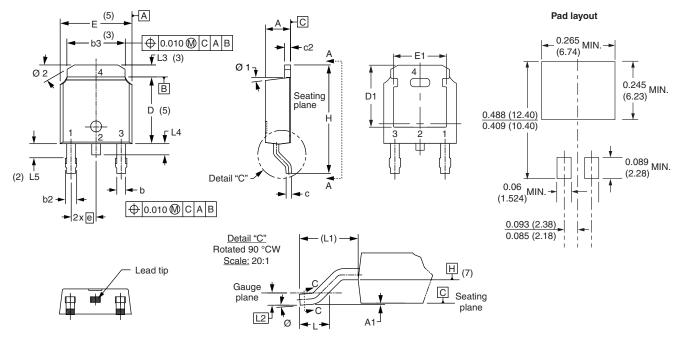
ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA04SD60S-M3	75	3000	Antistatic plastic tube						
VS-HFA04SD60STR-M3	2000	2000	13" diameter reel						
VS-HFA04SD60SL-M3	3000	3000	13" diameter reel						
VS-HFA04SD60SR-M3	3000	3000	13" diameter reel						

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95016						
Part marking information	www.vishay.com/doc?95176						
Packaging information	www.vishay.com/doc?95033						



D-PAK (TO-252AA)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		HES NOTES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	2.18	2.39	0.086	0.094			е	2.29	BSC	0.090	BSC	
A1	-	0.13	-	0.005			Н	9.40	10.41	0.370	0.410	
b	0.64	0.89	0.025	0.035			L	1.40	1.78	0.055	0.070	
b2	0.76	1.14	0.030	0.045			L1	2.74	BSC	0.108	REF.	
b3	4.95	5.46	0.195	0.215	3		L2	0.51	BSC	0.020	BSC	
с	0.46	0.61	0.018	0.024			L3	0.89	1.27	0.035	0.050	3
c2	0.46	0.89	0.018	0.035			L4	-	1.02	-	0.040	
D	5.97	6.22	0.235	0.245	5		L5	1.14	1.52	0.045	0.060	2
D1	5.21	-	0.205	-	3		Ø	0°	10°	0°	10°	
E	6.35	6.73	0.250	0.265	5		Ø1	0°	15°	0°	15°	
E1	4.32	-	0.170	-	3		Ø2	25°	35°	25°	35°	

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension uncontrolled in L5

⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad

⁽⁴⁾ Section C - C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip

(5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁶⁾ Dimension b1 and c1 applied to base metal only

⁽⁷⁾ Datum A and B to be determined at datum plane H

⁽⁸⁾ Outline conforms to JEDEC outline TO-252AA

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